IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of	Group Art Unit:				
Keith B. Kahen	Examiner:				
ORGANIC VERTICAL CAVITY LASER ARRAY DEVICE WITH VARYING PIXEL SIZES Serial No. To be assigned Filed 18 July 2003	Express Mail Label No. EV293538245US Date: 18 July 2003				
Commissioner for Patents P.O. Box 1450 Alexandria, VA. 22313-1450 Sir:	TATEMENT FOR CONSIDERATION				
	DER 37 C.F.R. 1.97-1.99				
by the Patent and Trademark Office in reabove-described application. In complia listed in the enclosed Form PTO-1449.	ne Patent and Trademark Office make of Unless otherwise indicated, a full text documents not in English, an English guage patent or publication may be ilable, a concise explanation of the				
This Information Disclos submitted according to the following sel	ure Statement (hereinafter "Statement") is ected paragraph:				
the filing date of the applicat mailing of a first Office action	under §1.97(b) within three months of ion (other than a CPA), or before the on on the merits or before the mailing of a ling of a request for continued				
mailing date of any of a final that otherwise closes prosecu fee required by §1.17(p) to E	under §1.97(c), with fee, prior to the action, a notice of allowance or an action ation in the application. Please charge the astman Kodak Company Deposit Order A duplicate copy of this Certification is				

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IV.	certification and action charge Depo	on, a notice of allowance (but priorition that otherwise closes prosed ge the fee required by §1.17(p) to osit Order Account No. 05-0225. ification is enclosed. The undersi	Iter the mailing date of either a final for to payment of the issue fee) or ecution in the application. Please to Eastman Kodak Company A duplicate copy of this	
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Raymond	L. Ow	vens/phw //	Attorney for Applicants	_

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Enclosures

Attorney for Applicants Registration No. 22,363

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